

CURRENT CARRIER SCATTERING IN EPITAXIAL
PbSe FILMS

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S u m m a r y

The dependence of the current carrier mobility in the epitaxial PbSe films deposited on the mica substrates on the film thickness within the interval 0.1–2.0 μm and at temperatures 77–300 K has been studied. A contribution to the mobility caused by the current carrier scattering by the surface has been calculated. The residual mobility and the dominating mechanisms of the current carrier scattering at various film thicknesses have been determined.